Jeomoh Kim

List of Publications by Year
in descending order

15 papers	526 citations	840776 11 h-index	996975 15 g-index
15 all docs	15 docs citations	15 times ranked	665 citing authors

#	Article	IF	Citations
1	Improvement of peak quantum efficiency and efficiency droop in III-nitride visible light-emitting diodes with an InAlN electron-blocking layer. Applied Physics Letters, 2010, 96, .	3.3	183
2	Efficiency droop due to electron spill-over and limited hole injection in III-nitride visible light-emitting diodes employing lattice-matched InAlN electron blocking layers. Applied Physics Letters, 2012, 101, .	3.3	80
3	Origins of unintentional incorporation of gallium in AlInN layers during epitaxial growth, part I: Growth of AlInN on AlN and effects of prior coating. Journal of Crystal Growth, 2014, 388, 137-142.	1.5	45
4	Origins of unintentional incorporation of gallium in InAlN layers during epitaxial growth, part II: Effects of underlying layers and growth chamber conditions. Journal of Crystal Growth, 2014, 388, 143-149.	1.5	44
5	Al_xGa_{1â^'x}N Ultraviolet Avalanche Photodiodes With Avalanche Gain Greater Than 10^{5}. IEEE Photonics Technology Letters, 2015, 27, 642-645.	2.5	38
6	Uniform and Reliable GaN <italic>p-i-n</italic> Ultraviolet Avalanche Photodiode Arrays. IEEE Photonics Technology Letters, 2016, 28, 2015-2018.	2.5	26
7	Comparison of AlGaN pâ€“iâ€“n ultraviolet avalanche photodiodes grown on free-standing GaN and sapphire substrates. Applied Physics Express, 2015, 8, 122202.	2.4	23
8	p-i-p-i-n Separate Absorption and Multiplication Ultraviolet Avalanche Photodiodes. IEEE Photonics Technology Letters, 2018, 30, 181-184.	2.5	23
9	Temperature-Dependent Characteristics of GaN Homojunction Rectifiers. IEEE Transactions on Electron Devices, 2015, 62, 2679-2683.	3.0	19
10	High-Responsivity GaN/InGaN Heterojunction Phototransistors. IEEE Photonics Technology Letters, 2016, 28, 2035-2038.	2.5	17
11	Temperature-Dependent Resonance Energy Transfer from Semiconductor Quantum Wells to Graphene. Nano Letters, 2015, 15, 896-902.	9.1	12
12	Direct periodic patterning of GaN-based light-emitting diodes by three-beam interference laser ablation. Applied Physics Letters, 2014, 104, 141105.	3.3	9
13	Effect of latticeâ€matched InAlGaN electronâ€blocking layer on hole transport and distribution in InGaN/GaN multiple quantum wells of visible lightâ€emitting diodes. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1296-1301.	1.8	3
14	Improved Hole Transport by ${m p}hbox{-}{m In}_{x}{m Ga}_{1-x}{m N}$ Layer in Multiple Quantum Wells of Visible LEDs. IEEE Photonics Technology Letters, 2013, 25, 1789-1792.	2.5	2
15	Radiative recombination in GaN/InGaN heterojunction bipolar transistors. Applied Physics Letters, 2015, 107, 242104.	3.3	2